The HD74LS170 is organized as 4 words of 4 bits each and separate on-chip decoding is provided for addressing the four word locations to either write-in or retrieve data. This permits simultaneous writing into one location and reading from another word location.

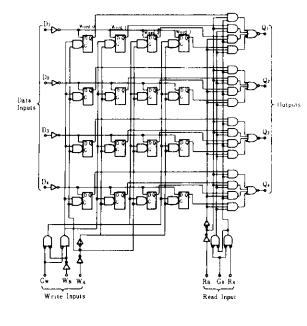
Four data inputs are available which are used to supply the 4-bit word to be stored. Location of the word is determined by the write-address inputs A and B in conjunction with a write-enable signal.

Data applied at the inputs should be in its true form. That is, if a high-level signal is desired from the output, a high level is applied at the data input for that particular bit location. The latch inputs are arranged so that new data will be accepted only if both internal address gate inputs are high. When this condition exists, data at the D input is transferred to the latch output. When the write-enable input, G_W , is high, the data inputs are inhibited and their levels can cause no change in the information stored in the internal latches.

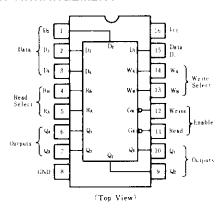
When the read-enable input, G_R , is high, the data outputs are inhibited and remain high, the individual address lines permit direct acquisition of data stored in any four of the latches. Four individual decoding gates are used to complete the address for reading a word.

When the read address is made in conjunction with the readenable signal the word appears at the four outputs.

■BLOCK DIAGRAM



■PIN ARRANGEMENT



■FUNCTION TABLE

W	rite Inpu	ts	Word					
W _B	WA	Gw	0	l	2	3		
L	L	L	Q D	Q_6	\mathbf{Q}_{o}	Q_0		
L	Н	L	Q_0	Q-D	Q_c	Q ₀		
Н	L	I.	\mathbf{Q}_0	Q ₀	Q=D	\mathbf{Q}_{0}		
Н	Н	1.	Q_0	Q_n	\mathbf{Q}_{0}	Q=])		
×	×	H	Q_0	Q ₀	Qu	$Q_{\mathfrak{s}}$		

F	Read Input	s		Outputs					
W _B	W _A	Gw	0	1	2	3			
1.	L	L	W ₀ B ₁	W n B2	W ₀ B₃	W₀ B₊			
1.	Н	I.	W_1/B_1	$W_{\perp} B_2$	$W_{\perp} B_3$	W ₊ B _•			
Н	l.	L	W 2 B1	W _z B ₂	W ₂ B ₃	W ₂ B ₄			
Н	Н	L	W ₃ B ₁	W ₃ B ₂	W ₃ B ₃	W 3 B 4			
>:	×	Н	Н	Н	Н	Н			

Notes: H = high level, L = low level, X = irrelevant.

(Q=D) = The four selected internal flip-flop outputs will assume the states applied to the four external data inputs.

Q₀ = The level of Q before the indicated input conditions were established.

WoB, = The first bit of word 0, etc.

■ RECOMMENDED OPERATING CONDITIONS

Item Supply Voltage Output Voltage		Symbol	min	typ	max	Unit
		Vcc	4.75	5	5.25	V
		Von			5.5	
Output (Current	Iou	_		8	mA
Pulse	Read enable		25		T	
width	Write enable	- tw	60	_		ns
Setup	Data input		10		-	「 <u> </u>
Time	Write select	- t.,	15	_	T -	ns
Hold	Data input	1.	15			
Time	Write select	th	5		<u> </u>	ns
Latch time		Linteh	60	_	_	ns

ELECTRICAL CHARACTERISTICS $(Ta = -20 \sim +75^{\circ}C)$

Item		Symbol	Test Conditi	on	min	typ*	max	Unit
Input Voltage		V _{tH}			2.0			V
		V_{IL}			_		0.8	V
Output Cu	ırrent	I _{OH}	Vcc-4.75V, VoH-5.5V, VIL	-0.8V, VIH-2V		_	100	μΑ
			$V_{CC} = 4.75 \text{V}, V_{IH} = 2 \text{V},$	IoL-4mA	_		0.4	V
Output Vo	oltage	Vol	$V_{IL}=0.8V$ $I_{OL}=8$				0.5	
Any D. F	Any D, R or W		17 - 0-17 17 0 717		_		20	A
	GR OF GW	IIH	$V_{cc} = 5.25 \text{V}, V_{i} = 2.7 \text{V}$			_	40	μΑ
Input	Any D, R or W	<u> </u>			_		-0.4	
Current	GR or Gw	I _{IL}	$V_{cc}=5.25$ V, $V_{i}=0.4$ V				-0.8	mA
	Any D, R or W				. —		0.1	
	GR or Gw	I_{I}	V_{cc} -5.25V, V_i -7V		_		0.2	mA
Supply Current Icc		Icc**	Vcc-5.25V			25	40	mA
		Vik	$V_{cc} = 4.75 \text{V}, I_{IN} = -18 \text{mA}$			_	-1.5	v

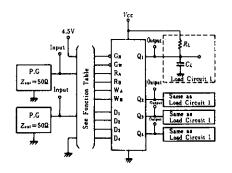
[•] VCC=5V, Ta=25°C

Typical I_{CC} shown is an average for 50% duty cycle. Maximum I_{CC} is guaranteed for the following worst case conditions: 4.5V is applied to all data inputs and both enable inputs, all address inputs are grounded, and all outputs are open.

ESWITCHING CHARACTERISTICS $(V_{cc}=5V, Ta=25^{\circ}C)$

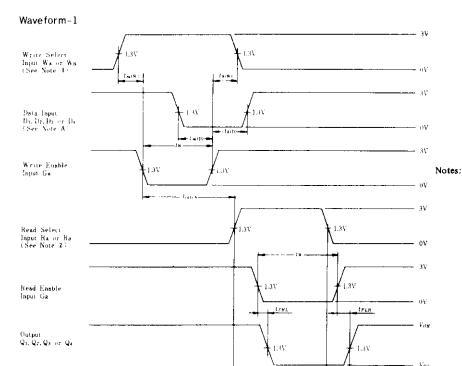
Item	Symbol	Inputs	Outputs	Test Conditions	min	typ	max	Unit	
	tplH	Read		$C_L = 15 \text{pF}$ $R_L = 2 \text{k}\Omega$	T - "	20	30	ns	
	tpHL	enable	$Q_1 \sim Q_4$			20	30		
Propagation Delay Time	I PLH	Read	$Q_1 \sim Q_4$		-	25	40		
	t PH L	select			_	24	40		
	tPLH	Write	$Q_1\!\sim\!Q_4$			30	45		
	tpHL	enable		Q1~Q1 Q1~Q1			_	26	40
	tpLH	_	$Q_1 \sim Q_4$			1		30	45
	tpHL	Data					22	30	1

ETESTING METHOD



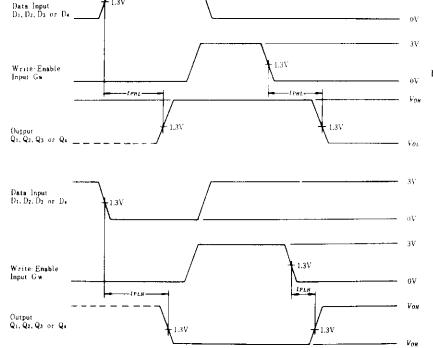
1. C_L includes probe and jig capacitance. 2. All diodes are 1S2074 \bigoplus . Notes:

HD74LS170



- High-level input pulses at the select and data inputs are illustrated in Waveform-1; however, times associated with low-level pulses are measured from the same reference points.
- When measuring delay times from a read-select input, the readenable input is low. When measuring delay times from the read-enable input, both read-select inputs have been established at steady states.
- Input pulse; t_{TLH} ≤ 15ns, t_{THL} ≤ 6ns, PRR ≤ 1MHz, duty cycle 50%.

Waveform-2

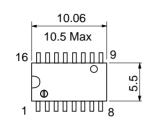


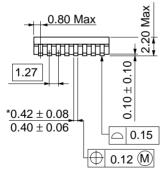
Note: In Waveform-2, each select address is tested. Prior to the start of each of the above tests, both write and read address inputs are stabilized with W_A = R_A and W_B = R_B . During the test G_R is low.

3V

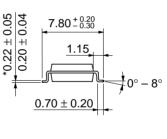
Unit: mm 19.20 20.00 Max 16 7.40 Max 6.30 1.3 1.11 Max 7.62 5.06 Max 2.54 Min 0.51 Min $0.25^{+0.13}_{-0.05}$ 0.48 ± 0.10 2.54 ± 0.25 $0^{\circ} - 15^{\circ}$ Hitachi Code DP-16 **JEDEC** Conforms EIAJ Conforms Weight (reference value) 1.07 g

Unit: mm





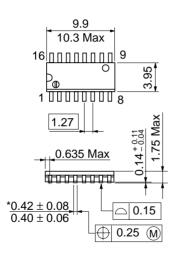


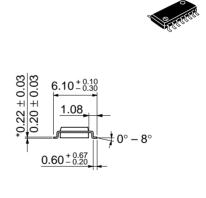


Hitachi Code	FP-16DA
JEDEC	_
EIAJ	Conforms
Weight (reference value)	0.24 g

*Dimension including the plating thickness
Base material dimension

Unit: mm





*Dimension including the plating thickness
Base material dimension

Hitachi Code	FP-16DN
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	0.15 g

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